



November 2014

FDMS8570S

N-Channel PowerTrench® SyncFET™

25 V, 60 A, 2.8 mΩ

Features

- Max $r_{DS(on)}$ = 2.8 mΩ at $V_{GS} = 10$ V, $I_D = 24$ A
- Max $r_{DS(on)}$ = 3.1 mΩ at $V_{GS} = 4.5$ V, $I_D = 22$ A
- High performance technology for extremely low $r_{DS(on)}$
- SyncFET™ Schottky Body Diode
- RoHS Compliant



General Description

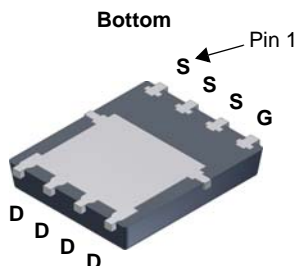
This N-Channel SyncFET™ is produced using Fairchild Semiconductor's advanced PowerTrench® process. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Telecom Secondary Side Rectification
- High End Server/Workstation Vcore Low Side

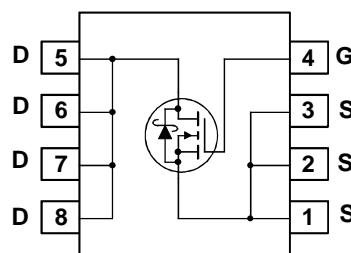


Top



Bottom

Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|--|-------------|------------------|
| V_{DS} | Drain to Source Voltage | 25 | V |
| V_{GS} | Gate to Source Voltage | 12 | V |
| I_D | Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$ | 60 | A |
| | -Continuous $T_A = 25^\circ\text{C}$ (Note 1a) | 24 | |
| | -Pulsed | 100 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 45 | mJ |
| P_D | Power Dissipation $T_C = 25^\circ\text{C}$ | 48 | W |
| | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) | 2.5 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case $T_C = 25^\circ\text{C}$ | 2.6 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 50 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------|----------|-----------|------------|------------|
| 100D | FDMS8570S | Power 56 | 13" | 12 mm | 3000 units |

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|----|----|-----------|------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$ | 25 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 10\text{ mA}$, referenced to $25\text{ }^{\circ}\text{C}$ | | 23 | | mV/ $^{\circ}\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 500 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = +12\text{ V/-8 V}$, $V_{DS} = 0\text{ V}$ | | | ± 100 | nA |

On Characteristics

| | | | | | | |
|--|--|--|-----|-----|-----|------------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$ | 1.1 | 1.5 | 2.2 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 10\text{ mA}$, referenced to $25\text{ }^{\circ}\text{C}$ | | -3 | | mV/ $^{\circ}\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}$, $I_D = 24\text{ A}$ | | 2.1 | 2.8 | m Ω |
| | | $V_{GS} = 4.5\text{ V}$, $I_D = 22\text{ A}$ | | 2.4 | 3.1 | |
| | | $V_{GS} = 10\text{ V}$, $I_D = 24\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$ | | 2.9 | 3.9 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}$, $I_D = 24\text{ A}$ | | 215 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|------|--|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 13\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | | 2825 | | pF |
| C_{oss} | Output Capacitance | | | 662 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 94 | | pF |
| R_g | Gate Resistance | | | 0.8 | | Ω |

Switching Characteristics

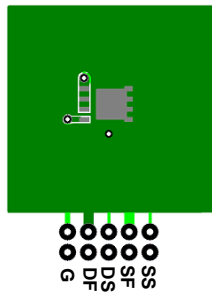
| | | | | | | |
|--------------|-------------------------------|--|---|-----|--|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 13\text{ V}$, $I_D = 24\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$ | | 11 | | ns |
| t_r | Rise Time | | | 4 | | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 33 | | ns |
| t_f | Fall Time | | | 3 | | ns |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to }10\text{ V}$ | $V_{DD} = 13\text{ V}$, $I_D = 24\text{ A}$ | 42 | | nC |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to }4.5\text{ V}$ | | 22 | | nC |
| Q_{gs} | Gate to Source Gate Charge | | | 6.4 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | 4.4 | | nC |

Drain-Source Diode Characteristics

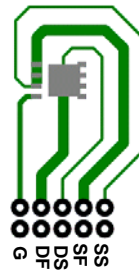
| | | | | | | |
|----------|---------------------------------------|--|--|-----|-----|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}$, $I_S = 2\text{ A}$ (Note 2) | | 0.6 | 0.8 | V |
| | | $V_{GS} = 0\text{ V}$, $I_S = 24\text{ A}$ (Note 2) | | 0.8 | 1.2 | |
| t_{rr} | Reverse Recovery Time | $I_F = 24\text{ A}$, $di/dt = 300\text{ A}/\mu\text{s}$ | | 22 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 19 | | nC |

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $50\text{ }^{\circ}\text{C/W}$ when mounted on a
1 in² pad of 2 oz copper



b) $125\text{ }^{\circ}\text{C/W}$ when mounted on
a minimum pad of 2 oz
copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. E_{AS} of 45 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 0.4\text{ mH}$, $I_{AS} = 15\text{ A}$, $V_{DD} = 23\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 23.8\text{ A}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

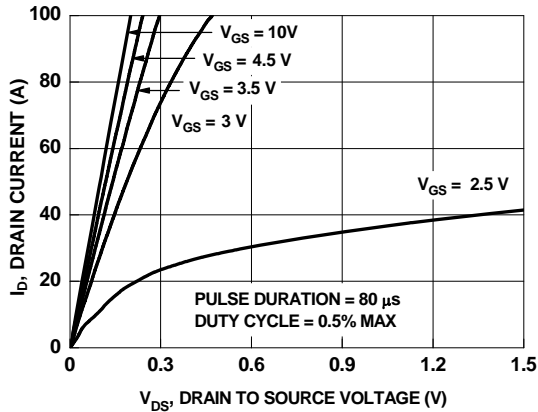


Figure 1. On Region Characteristics

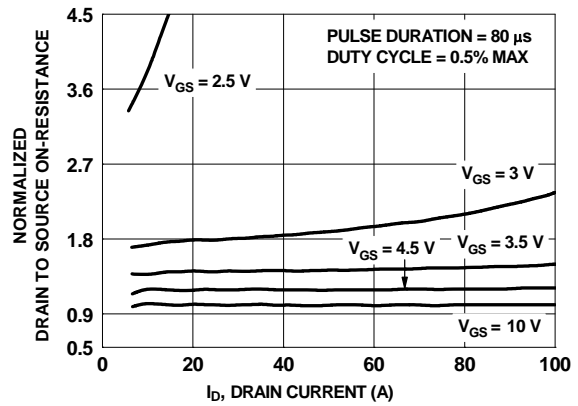


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

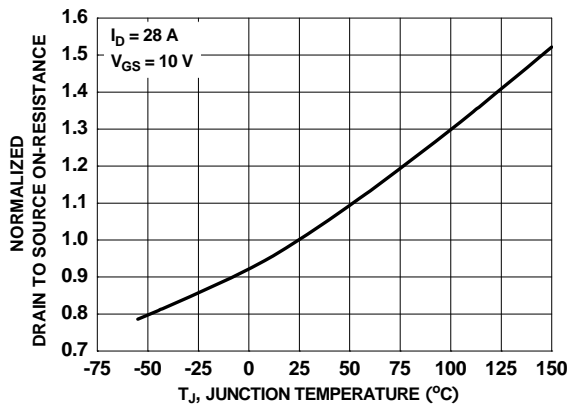


Figure 3. Normalized On Resistance vs Junction Temperature

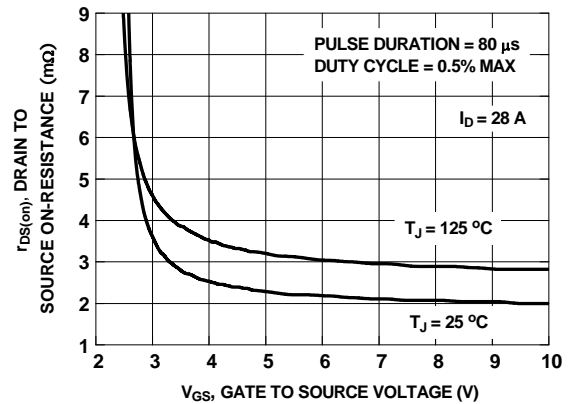


Figure 4. On-Resistance vs Gate to Source Voltage

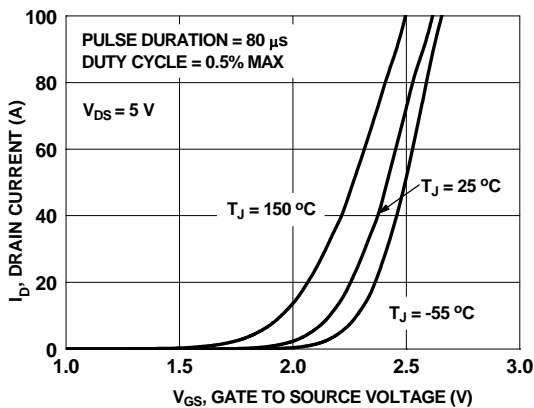


Figure 5. Transfer Characteristics

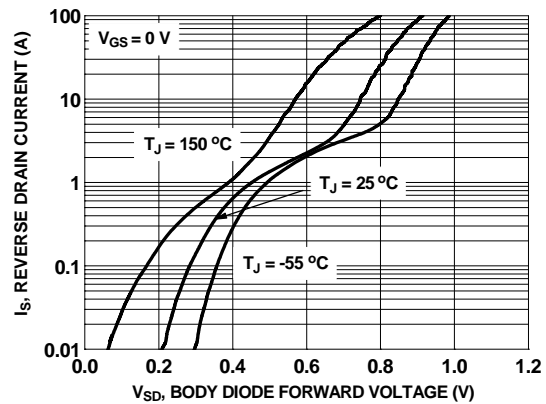


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

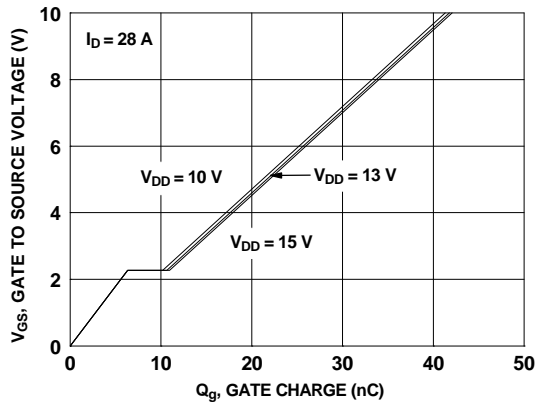


Figure 7. Gate Charge Characteristics

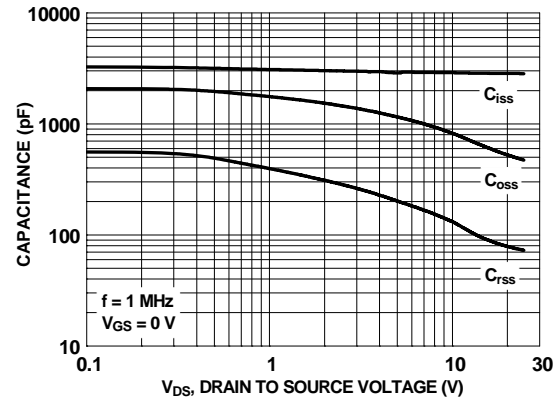


Figure 8. Capacitance vs Drain to Source Voltage

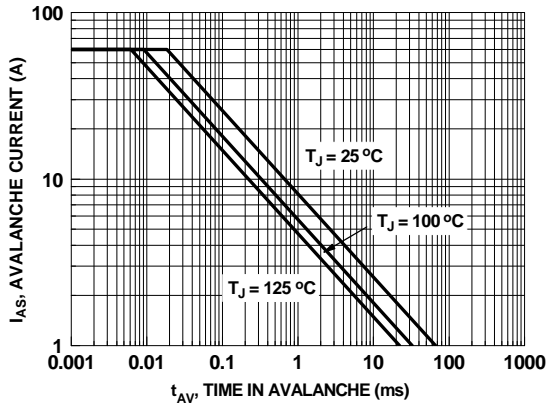


Figure 9. Unclamped Inductive Switching Capability

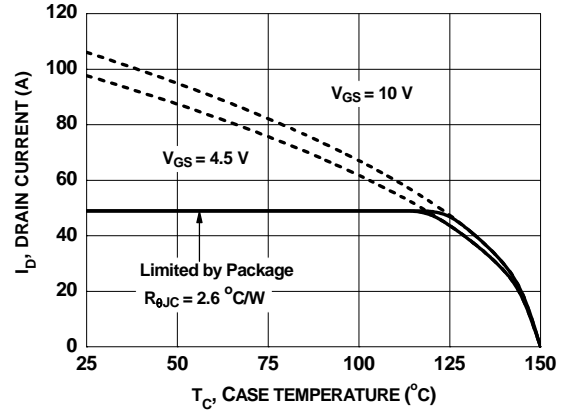


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

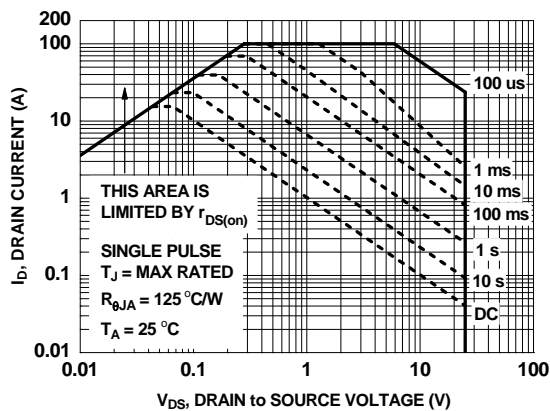


Figure 11. Forward Bias Safe Operating Area

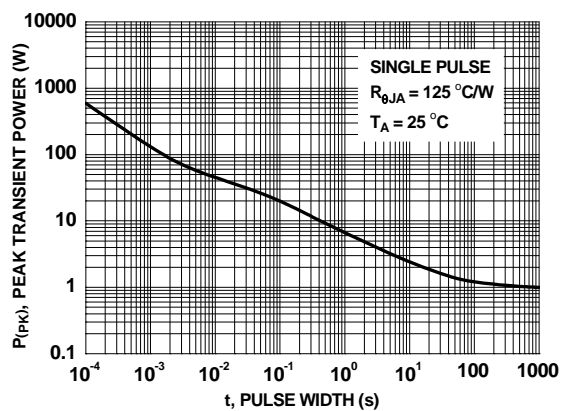


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

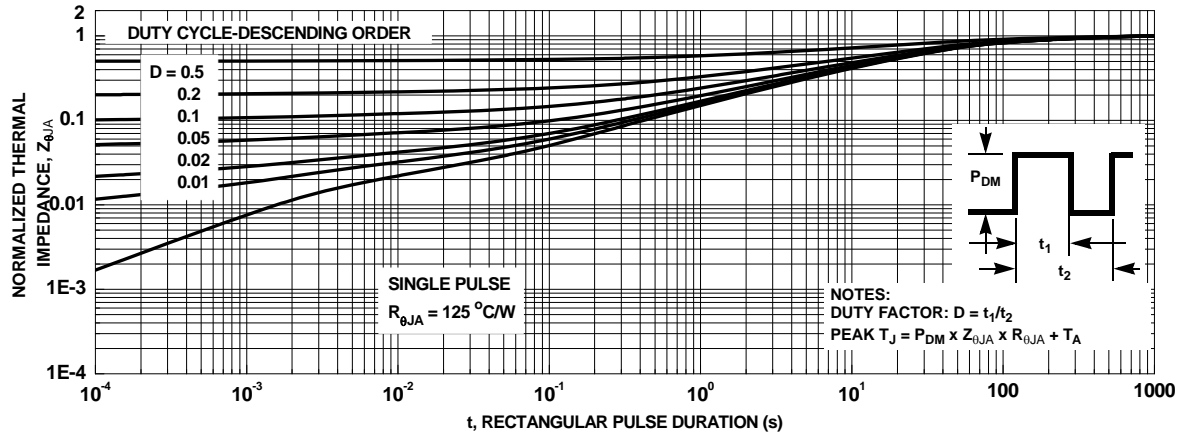


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET™ Schottky body diode Characteristics

Fairchild's SyncFET™ process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS8570S.

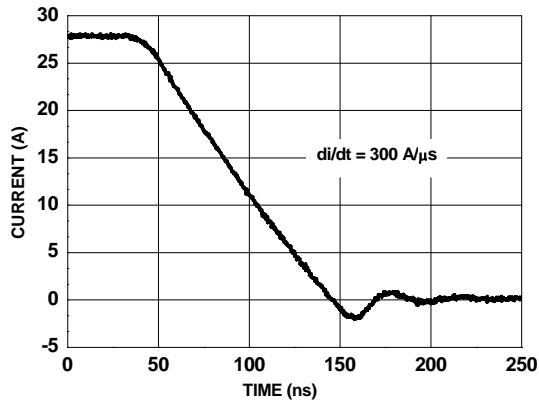


Figure 14. FDMS8570S SyncFET™ body diode reverse recovery characteristic

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

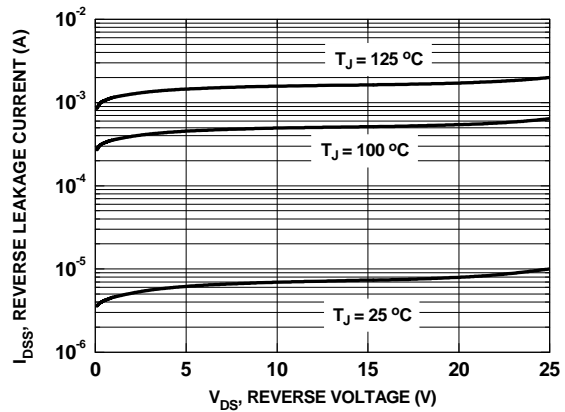
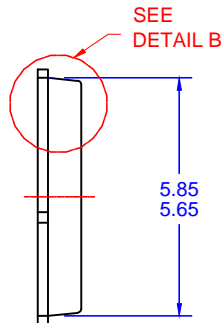


Figure 15. SyncFET™ body diode reverse leakage versus drain-source voltage

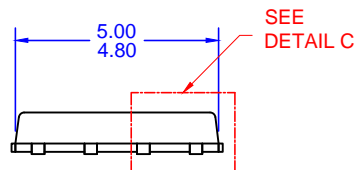
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



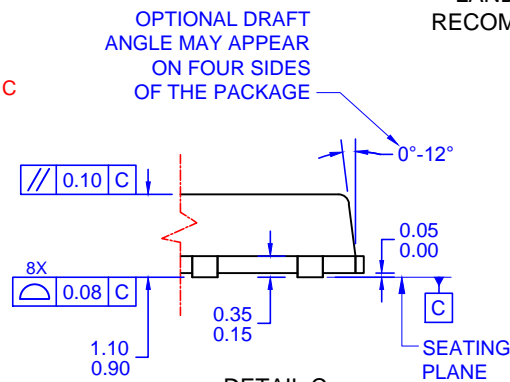
TOP VIEW



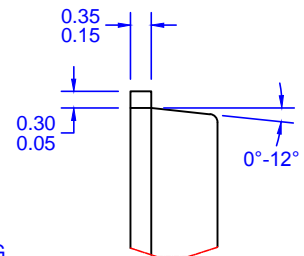
LAND PATTERN
RECOMMENDATION



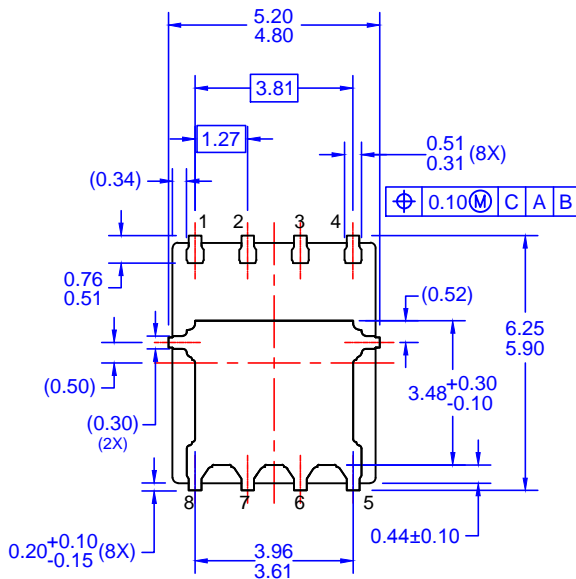
SIDE VIEW



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA.
- DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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